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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

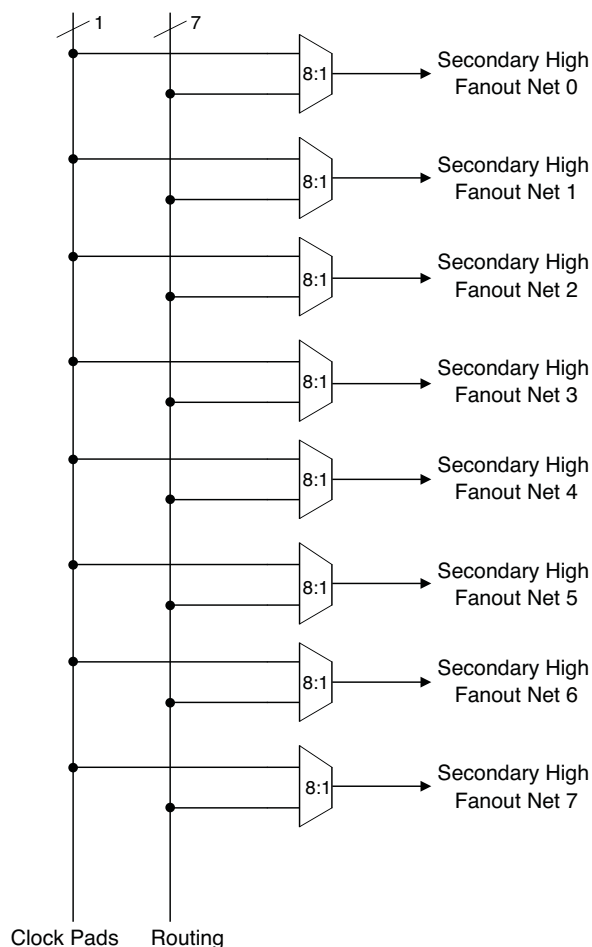
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	160
Number of Logic Elements/Cells	1280
Total RAM Bits	65536
Number of I/O	79
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-1200ze-2tg100c

Figure 2-6. Secondary High Fanout Nets for MachXO2 Devices



sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The MachXO2-640U, MachXO2-1200/U and larger devices have one or more sysCLOCK PLL. CLKI is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. CLKFB is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The MachXO2 sysCLOCK PLLs support high resolution (16-bit) fractional-N synthesis. Fractional-N frequency synthesis allows the user to generate an output clock which is a non-integer multiple of the input frequency. For more information about using the PLL with Fractional-N synthesis, please see TN1199, [MachXO2 sysCLOCK PLL Design and Usage Guide](#).

Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The output dividers may also be cascaded together to generate low frequency clocks. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the MachXO2 clock distribution network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-7.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.

More information on the input gearbox is available in TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#).

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDR4 (8:1) gearbox or as two ODDR2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDR4(8:1): D[7:0]		
GDDR2(4:1)(IOL-A): D[3:0]		
GDDR2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-17 shows the output gearbox block diagram.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

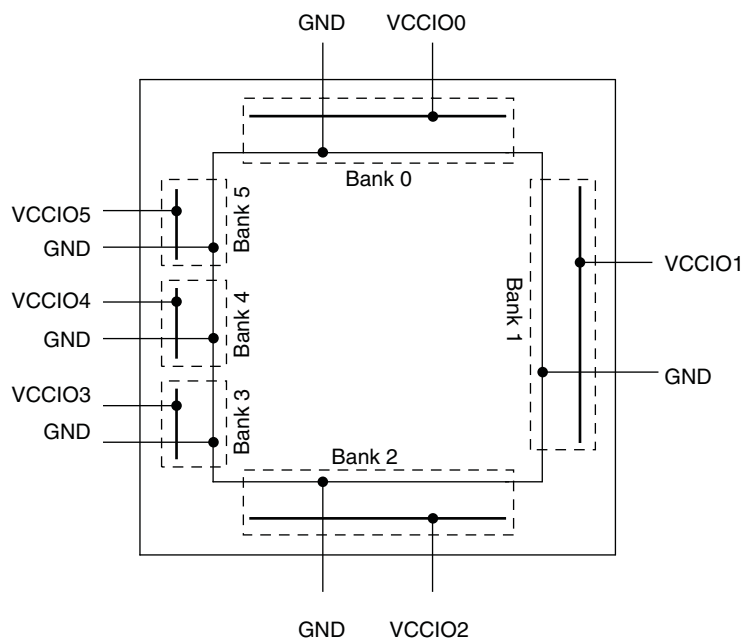
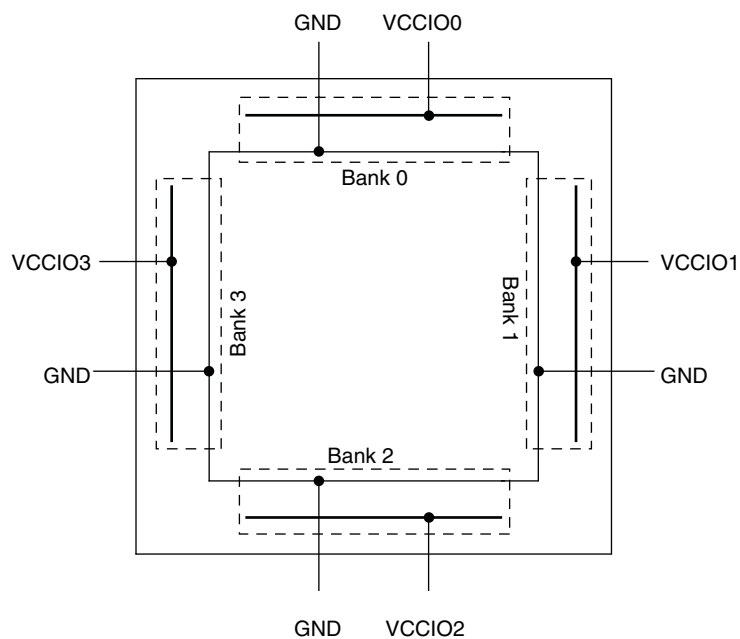


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



For more details on these embedded functions, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I²C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC} .

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Configuration and Testing

This section describes the configuration and testing features of the MachXO2 family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, [Boundary Scan Testability with Lattice sysIO Capability](#) and TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#).

Device Configuration

All MachXO2 devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I²C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO2 device:

1. Internal Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I²C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1204, [MachXO2 Programming and Configuration Usage Guide](#) for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO2 devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip Flash memory, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip Flash memory. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) for details.



MachXO2 Family Data Sheet

DC and Switching Characteristics

March 2017

Data Sheet DS1035

Absolute Maximum Ratings^{1, 2, 3}

	MachXO2 ZE/HE (1.2 V)	MachXO2 HC (2.5 V / 3.3 V)
Supply Voltage V_{CC}	–0.5 V to 1.32 V	–0.5 V to 3.75 V
Output Supply Voltage V_{CCIO}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
I/O Tri-state Voltage Applied ^{4, 5}	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Dedicated Input Voltage Applied ⁴	–0.5 V to 3.75 V	–0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature (T_J)	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice [Thermal Management](#) document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of –2 V to ($V_{IHMAX} + 2$) volts is permitted for a duration of <20 ns.
5. The dual function I²C pins SCL and SDA are limited to –0.25 V to 3.75 V or to –0.3 V with a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
V_{CC}^1	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
	Core Supply Voltage for 2.5 V / 3.3 V Devices	2.375	3.6	V
$V_{CCIO}^{1, 2, 3}$	I/O Driver Supply Voltage	1.14	3.6	V
t_{JCOM}	Junction Temperature Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature Industrial Operation	–40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both the same voltage, they must also be the same supply.
2. See recommended voltages by I/O standard in subsequent table.
3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

Power Supply Ramp Rates¹

Symbol	Parameter	Min.	Typ.	Max.	Units
t_{RAMP}	Power supply ramp rates for all power supplies.	0.01	—	100	V/ms

1. Assumes monotonic ramp rates.

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max. ¹	Units
N_{PROG}	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC} (MAX)$, $0 < V_{CCIO} < V_{CCIO} (MAX)$.
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

Static Supply Current – HC/HE Devices^{1, 2, 3, 6}

Symbol	Parameter	Device	Typ. ⁴	Units
I_{CC}	Core Power Supply	LCMXO2-256HC	1.15	mA
		LCMXO2-640HC	1.84	mA
		LCMXO2-640UHC	3.48	mA
		LCMXO2-1200HC	3.49	mA
		LCMXO2-1200UHC	4.80	mA
		LCMXO2-2000HC	4.80	mA
		LCMXO2-2000UHC	8.44	mA
		LCMXO2-4000HC	8.45	mA
		LCMXO2-7000HC	12.87	mA
		LCMXO2-2000HE	1.39	mA
		LCMXO2-4000HE	2.55	mA
		LCMXO2-7000HE	4.06	mA
I_{CCIO}	Bank Power Supply ⁵ $V_{CCIO} = 2.5\text{ V}$	All devices	0	mA

- For further information on supply current, please refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).
- Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip oscillator is off, on-chip PLL is off.
- Frequency = 0 MHz.
- $T_J = 25\text{ }^{\circ}\text{C}$, power supplies at nominal voltage.
- Does not include pull-up/pull-down.
- To determine the MachXO2 peak start-up current data, use the Power Calculator tool.

Programming and Erase Flash Supply Current – HC/HE Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. ⁵	Units
I_{CC}	Core Power Supply	LCMXO2-256HC	14.6	mA
		LCMXO2-640HC	16.1	mA
		LCMXO2-640UHC	18.8	mA
		LCMXO2-1200HC	18.8	mA
		LCMXO2-1200UHC	22.1	mA
		LCMXO2-2000HC	22.1	mA
		LCMXO2-2000UHC	26.8	mA
		LCMXO2-4000HC	26.8	mA
		LCMXO2-7000HC	33.2	mA
		LCMXO2-2000HE	18.3	mA
		LCMXO2-2000UHE	20.4	mA
		LCMXO2-4000HE	20.4	mA
		LCMXO2-7000HE	23.9	mA
I_{CCIO}	Bank Power Supply ⁶	All devices	0	mA

- For further information on supply current, please refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).
- Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
- Typical user pattern.
- JTAG programming is at 25 MHz.
- $T_J = 25\text{ }^{\circ}\text{C}$, power supplies at nominal voltage.
- Per bank. $V_{CCIO} = 2.5\text{ V}$. Does not include pull-up/pull-down.

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max. ⁴ (mA)	I_{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
							24	-24
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.8	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
					0.2	$V_{CCIO} - 0.2$	8	-8
							12	-12
LVCMOS 1.2	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-2
							8	-6
							0.1	-0.1
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI	-0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	-0.5
SSTL25 Class I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	8	8
SSTL25 Class II	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	NA	NA	NA	NA
SSTL18 Class I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
SSTL18 Class II	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	NA	NA	NA	NA
HSTL18 Class I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
HSTL18 Class II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS25R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

Typical Building Block Function Performance – HC/HE Devices¹

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	-6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Typical Building Block Function Performance – ZE Devices¹

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	–3 Timing	Units
Basic Functions		
16-bit decoder	13.9	ns
4:1 MUX	10.9	ns
16:1 MUX	12.0	ns

Register-to-Register Performance

Function	–3 Timing	Units
Basic Functions		
16:1 MUX	191	MHz
16-bit adder	134	MHz
16-bit counter	148	MHz
64-bit counter	77	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	90	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	214	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

MachXO2 External Switching Characteristics – HC/HE Devices^{1, 2, 3, 4, 5, 6, 7}

Over Recommended Operating Conditions

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clocks									
f _{MAX_PRI} ⁸	Frequency for Primary Clock Tree	All MachXO2 devices	—	388	—	323	—	269	MHz
t _{W_PRI}	Clock Pulse Width for Primary Clock	All MachXO2 devices	0.5	—	0.6	—	0.7	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	MachXO2-256HC-HE	—	912	—	939	—	975	ps
		MachXO2-640HC-HE	—	844	—	871	—	908	ps
		MachXO2-1200HC-HE	—	868	—	902	—	951	ps
		MachXO2-2000HC-HE	—	867	—	897	—	941	ps
		MachXO2-4000HC-HE	—	865	—	892	—	931	ps
		MachXO2-7000HC-HE	—	902	—	942	—	989	ps
Edge Clock									
f _{MAX_EDGE} ⁸	Frequency for Edge Clock	MachXO2-1200 and larger devices	—	400	—	333	—	278	MHz
Pin-LUT-Pin Propagation Delay									
t _{PD}	Best case propagation delay through one LUT-4	All MachXO2 devices	—	6.72	—	6.96	—	7.24	ns
General I/O Pin Parameters (Using Primary Clock without PLL)									
t _{CO}	Clock to Output – PIO Output Register	MachXO2-256HC-HE	—	7.13	—	7.30	—	7.57	ns
		MachXO2-640HC-HE	—	7.15	—	7.30	—	7.57	ns
		MachXO2-1200HC-HE	—	7.44	—	7.64	—	7.94	ns
		MachXO2-2000HC-HE	—	7.46	—	7.66	—	7.96	ns
		MachXO2-4000HC-HE	—	7.51	—	7.71	—	8.01	ns
		MachXO2-7000HC-HE	—	7.54	—	7.75	—	8.06	ns
t _{SU}	Clock to Data Setup – PIO Input Register	MachXO2-256HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-640HC-HE	–0.06	—	–0.06	—	–0.06	—	ns
		MachXO2-1200HC-HE	–0.17	—	–0.17	—	–0.17	—	ns
		MachXO2-2000HC-HE	–0.20	—	–0.20	—	–0.20	—	ns
		MachXO2-4000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
		MachXO2-7000HC-HE	–0.23	—	–0.23	—	–0.23	—	ns
t _H	Clock to Data Hold – PIO Input Register	MachXO2-256HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-640HC-HE	1.75	—	1.95	—	2.16	—	ns
		MachXO2-1200HC-HE	1.88	—	2.12	—	2.36	—	ns
		MachXO2-2000HC-HE	1.89	—	2.13	—	2.37	—	ns
		MachXO2-4000HC-HE	1.94	—	2.18	—	2.43	—	ns
		MachXO2-7000HC-HE	1.98	—	2.23	—	2.49	—	ns

sysCLOCK PLL Timing (Continued)

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
$t_{\text{ROTATE_WD}}$	PHASESTEP Pulse Width		4	—	VCO Cycles

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. CLKOS as compared to CLKOP output for one phase step at the maximum VCO frequency. See TN1199, [MachXO2 sysCLOCK PLL Design and Usage Guide](#) for more details.
5. At minimum f_{PFD} . As the f_{PFD} increases the time will decrease to approximately 60% the value listed.
6. Maximum allowed jitter on an input clock. PLL unlock may occur if the input jitter exceeds this specification. Jitter on the input clock may be transferred to the output clocks, resulting in jitter measurements outside the output specifications listed in this table.
7. Edge Duty Trim Accuracy is a percentage of the setting value. Settings available are 70 ps, 140 ps, and 280 ps in addition to the default value of none.
8. Jitter values measured with the internal oscillator operating. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.

Flash Download Time^{1, 2}

Symbol	Parameter	Device	Typ.	Units
t_{REFRESH}	POR to Device I/O Active	LCMXO2-256	0.6	ms
		LCMXO2-640	1.0	ms
		LCMXO2-640U	1.9	ms
		LCMXO2-1200	1.9	ms
		LCMXO2-1200U	1.4	ms
		LCMXO2-2000	1.4	ms
		LCMXO2-2000U	2.4	ms
		LCMXO2-4000	2.4	ms
		LCMXO2-7000	3.8	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.

2. The Flash download time is measured starting from the maximum voltage of POR trip point.

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
t_{BTCODIS}	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	20	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
t_{BTUODIS}	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
t_{BTUPOEN}	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t _{PRGM}	PROGRAMN low pulse accept		55	—	ns
t _{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t _{INITL}	INITN low time	LCMXO2-256	—	30	μs
		LCMXO2-640	—	35	μs
		LCMXO2-640U/ LCMXO2-1200	—	55	μs
		LCMXO2-1200U/ LCMXO2-2000	—	70	μs
		LCMXO2-2000U/ LCMXO2-4000	—	105	μs
		LCMXO2-7000	—	130	μs
t _{DPPINIT}	PROGRAMN low to INITN low		—	150	ns
t _{DPPDONE}	PROGRAMN low to DONE low		—	150	ns
t _{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f _{MAX}	CCLK clock frequency		—	66	MHz
t _{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t _{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t _{STSU}	CCLK setup time		2	—	ns
t _{STH}	CCLK hold time		0	—	ns
t _{STCO}	CCLK falling edge to valid output		—	10	ns
t _{STOZ}	CCLK falling edge to valid disable		—	10	ns
t _{STOV}	CCLK falling edge to valid enable		—	10	ns
t _{SCS}	Chip select high time		25	—	ns
t _{SCSS}	Chip select setup time		3	—	ns
t _{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f _{MAX}	MCLK clock frequency		—	133	MHz
t _{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t _{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t _{STSU}	MCLK setup time		5	—	ns
t _{STH}	MCLK hold time		1	—	ns
t _{CSSPI}	INITN high to chip select low		100	200	ns
t _{MCLK}	INITN high to first MCLK edge		0.75	1	μs

	MachXO2-2000						MachXO2-2000U
	49 WLCSP	100 TQFP	132 csBGA	144 TQFP	256 caBGA	256 ftBGA	484 ftBGA
General Purpose I/O per Bank							
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
Dual Function I/O							
	24	31	33	33	33	33	37
High-speed Differential I/O							
Bank 0	5	4	8	9	14	14	18
Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups							
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484

High-Performance Commercial Grade Devices with Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256HC-4SG32C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	32	COM
LCMXO2-256HC-5SG32C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	32	COM
LCMXO2-256HC-6SG32C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	32	COM
LCMXO2-256HC-4SG48C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-256HC-5SG48C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-256HC-6SG48C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-256HC-4UMG64C	256	2.5 V / 3.3 V	–4	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-5UMG64C	256	2.5 V / 3.3 V	–5	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-6UMG64C	256	2.5 V / 3.3 V	–6	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-4TG100C	256	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-256HC-5TG100C	256	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-256HC-6TG100C	256	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-256HC-4MG132C	256	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-256HC-5MG132C	256	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-256HC-6MG132C	256	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640HC-4SG48C	640	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-640HC-5SG48C	640	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-640HC-6SG48C	640	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-640HC-4TG100C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-640HC-5TG100C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-640HC-6TG100C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-640HC-4MG132C	640	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-640HC-5MG132C	640	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-640HC-6MG132C	640	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640UHC-4TG144C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-5TG144C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-6TG144C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM

High-Performance Commercial Grade Devices without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100C	2112	1.2 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-5TG100C	2112	1.2 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-6TG100C	2112	1.2 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-4TG144C	2112	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-5TG144C	2112	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-6TG144C	2112	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-4MG132C	2112	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-5MG132C	2112	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-6MG132C	2112	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-4BG256C	2112	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-5BG256C	2112	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-6BG256C	2112	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-4FTG256C	2112	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-5FTG256C	2112	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-6FTG256C	2112	1.2 V	–6	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484C	2112	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-5FG484C	2112	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-6FG484C	2112	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-4TG144C	4320	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-5TG144C	4320	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-6TG144C	4320	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-4MG132C	4320	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-5MG132C	4320	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-6MG132C	4320	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-4BG256C	4320	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4MG184C	4320	1.2 V	–4	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5MG184C	4320	1.2 V	–5	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-6MG184C	4320	1.2 V	–6	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5BG256C	4320	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-6BG256C	4320	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4FTG256C	4320	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-5FTG256C	4320	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-6FTG256C	4320	1.2 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-4BG332C	4320	1.2 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-5BG332C	4320	1.2 V	–5	Halogen-Free caBGA	332	COM